

L Number	Hits	Search Text	DB	Time stamp
1	42115	anisotropic or anisotropical	USPAT; US-PGPUB	2003/05/14 09:51
2	29071	isotropic or isotropical	USPAT; US-PGPUB	2003/05/14 09:52
3	7380	(anisotropic or anisotropical) same (isotropic or isotropical)	USPAT; US-PGPUB	2003/05/14 09:53
4	2340873	side adj wall or side	USPAT; US-PGPUB	2003/05/14 09:53
5	185606	mask	USPAT; US-PGPUB	2003/05/14 09:53
6	7009	(side adj wall or side) near2 mask	USPAT; US-PGPUB	2003/05/14 09:54
7	234	((anisotropic or anisotropical) same (isotropic or isotropical)) and ((side adj wall or side) near2 mask)	USPAT; US-PGPUB	2003/05/14 09:54
8	3	("5770508" "5783475" "5817563").PN.	USPAT	2003/05/14 09:57
9	6	("4784965" "4855247" "5024959" "5153145" "5234850" "5472896").PN.	USPAT	2003/05/14 09:58
10	19	5770508.URPN.	USPAT	2003/05/14 09:59
11	2	6197648.URPN.	USPAT	2003/05/14 10:01
-	0	((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj sustrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:46
-	319	((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:34
-	0	((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (extension adj control)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:06
-	147	(((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (protective adj layer\$1 or (film\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:27
-	0	(((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (extension adj control)) and (sidewall or (side adj wall) with protection)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:24
-	0	(((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (extension adj control)) and (sidewall or (side adj wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:09
-	12	(((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (protective adj layer\$1 or (film\$1))) and (first adj impurit\$3) and (second adj impurit\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:11
-	392	((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:18
-	361	(((gate adj dielectric) same ((gate adj electrode)) with (semiconductor adj substrate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:19

-	333	((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:35
-	333	((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:24
-	138	((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate)) and (sidewall or (side adj wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:36
-	72	((((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate)) and (sidewall or (side adj wall))) and (protective adj layer\$1 or (film\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:37
-	103052	(metal adj oxide adj field adj effect adj transistor\$1 or (MOS adj transistor\$1) or (MOSFET))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:34
-	53	((metal adj oxide adj field adj effect adj transistor\$1 or (MOS adj transistor\$1) or (MOSFET))) same ((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:35
-	62	((metal adj oxide adj field adj effect adj transistor\$1 or (MOS adj transistor\$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:35
-	0	((((metal adj oxide adj field adj effect adj transistor\$1 or (MOS adj transistor\$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall))) same (protective adj layer\$1 or (film\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:38
-	20	((((metal adj oxide adj field adj effect adj transistor\$1 or (MOS adj transistor\$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) and (sidewall or (side adj wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:37
-	0	((((metal adj oxide adj field adj effect adj transistor\$1 or (MOS adj transistor\$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall))) and (protective adj layer\$1 or (film\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:40
-	2	((((metal adj oxide adj field adj effect adj transistor\$1 or (MOS adj transistor\$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:49
-	2	((((metal adj oxide adj field adj effect adj transistor\$1 or (MOS adj transistor\$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall))) and ((protective or (insulat\$3)) adj layer\$1 or (film\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:48

-	6770	gate adj dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:47
-	2280	(gate adj dielectric) same (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:48
-	803	((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat\$3) adj layer\$1 or (film\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:49
-	138	((((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat\$3) adj layer\$1 or (film\$1))) same (sidewall or (side adj wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:50
-	7	((((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat\$3) adj layer\$1 or (film\$1))) same (sidewall or (side adj wall))) same (sidewall or (side adj wall) adj mask\$1)) same (ion adj implant\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:53
-	105	(((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat\$3) adj layer\$1 or (film\$1))) same (sidewall or (side adj wall))) same (sidewall or (side adj wall) adj mask\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:54
-	2009	((438/301) or (438/303) or (438/305)).CCLS.	USPAT; US-PGPUB	2002/05/15 11:53
-	2774	((438/301) or (438/303) or (438/305)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 11:53
-	0	((((438/301) or (438/303) or (438/305)).CCLS.) and (dual adj spacer) same (implant\$3 with extension)	USPAT; US-PGPUB	2002/05/15 11:54
-	0	((((438/301) or (438/303) or (438/305)).CCLS.) and (dual adj spacer) same (implant\$3 with extension)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 11:56
-	1	("6287920").PN.	USPAT; US-PGPUB	2002/05/15 11:56
-	130	((438/301) or (438/303) or (438/305)).CCLS.) and (implant\$3 with extension)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 13:51
-	117	(mos adj transistor) or (metal adj oxide adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 17:05
-	297	((mos adj transistor) or (metal adj oxide adj transistor)) with (plural adj dop\$3) or ((first adj dop\$3) with (second adj dop\$3) with (third adj dop\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 17:08
-	4	((mos adj transistor) or (metal adj oxide adj transistor)) with (plural adj dop\$3) or ((first adj dop\$3) with (second adj dop\$3) with (third adj dop\$3))) with (ion adj implant\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 17:10

-	6	((mos adj transistor) or (metal adj oxide adj transistor)) with (plural adj dop\$3) or ((first adj dop\$3) with (second adj dop\$3) with (third adj dop\$3))) with extension	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 17:10
-	11	l adj shap\$2 with sidewall\$1 and extension\$1 and implant\$3 and dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/10 11:23
-	5	l adj shap\$2 with sidewall\$1 and extension\$1 and implant\$3 and dop\$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/09 18:16
-	16	l adj shap\$2 with sidewall\$1 and implant\$3 and dop\$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/09 18:16
-	0	l adj shap\$2 with sidewall\$1 and implant\$3 and dop\$3 and boron and boron adj florine	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/10 11:24
-	16	l adj shap\$2 with sidewall\$1 and implant\$3 and dop\$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/10 11:27
-	156	l adj shap\$2 and implant\$3 and dop\$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/10 11:28
-	68	l adj shap\$2 and mos and implant\$3 and dop\$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/10 11:49
-	166723	l adj shap\$2 mdd with implant\$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/10 11:50
-	1	l adj shap\$2 and mdd with implant\$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/10 11:51
-	0	l adj shap\$2 with side adj wall\$ and mdd with implant\$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/10 11:52
-	21	mos and mdd with implant\$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/10 11:52
-	15	pmos and mdd and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/10 12:42
-	56729	anisotrop\$\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/21 17:28
-	3	isostrop\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/21 17:28
-	28701	isotrop\$5	USPAT; US-PGPUB	2003/02/21 17:29

-	15001	anisotrop\$\$5 and isotrop\$5	USPAT;	2003/02/21 17:29
-	342575	gate	US-PGPUB	
-	4331	(anisotrop\$\$5 and isotrop\$5) and gate	USPAT;	2003/02/21 17:29
-	39483	ion adj implant\$5	US-PGPUB	2003/02/21 17:30
-	1875	((anisotrop\$\$5 and isotrop\$5) and gate) and (ion adj implant\$5)	USPAT;	2003/02/21 17:30
-	432112	extension	US-PGPUB	
-	367	((anisotrop\$\$5 and isotrop\$5) and gate) and (ion adj implant\$5)) and extension	USPAT;	2003/02/21 17:31
-	9	("4908326" "5234850" "5501997" "5541132" "5679589" "5770508" "5783475" "5863824" "6020242").PN.	USPAT	2003/02/21 17:57
-	2768	l adj shap\$2 same spacer\$1	USPAT;	2003/02/21 18:01
-	5	((((anisotrop\$\$5 and isotrop\$5) and gate) and (ion adj implant\$5)) and extension) and (l adj shap\$2 same spacer\$1)	US-PGPUB	2003/02/21 18:01